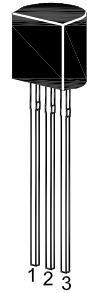


## BC546...BC550

### NPN Silicon Epitaxial Planar Transistor

for switching and AF amplifier application

These transistors are subdivided into three groups A, B and C according to their current gain.



1. Collector 2. Base 3. Emitter  
TO-92 Plastic Package

#### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Collector Base Voltage	$V_{CBO}$	80	V
BC546		50	
BC547, BC550 BC548, BC549		30	
Collector Emitter Voltage	$V_{CEO}$	65	V
BC546		45	
BC547, BC550 BC548, BC549		30	
Emitter Base Voltage	$V_{EBO}$	6	V
Collector Current (DC)	$I_C$	100	mA
Peak Collector Current	$I_{CM}$	200	mA
Total Power Dissipation	$P_{tot}$	500	mW
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 65 to + 150	$^\circ\text{C}$

#### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit	
DC Current Gain at $V_{CE} = 5\text{ V}$ , $I_C = 2\text{ mA}$	Current Gain Group A	$h_{FE}$	110	220	-
	B	$h_{FE}$	200	450	-
	C	$h_{FE}$	420	800	-
Collector Base Cutoff Current at $V_{CB} = 30\text{ V}$	$I_{CBO}$	-	15	nA	
Emitter Base Cutoff Current at $V_{EB} = 5\text{ V}$	$I_{EBO}$	-	100	nA	
Collector Base Breakdown Voltage at $I_C = 100\text{ }\mu\text{A}$	$V_{(BR)CBO}$	BC546	80	-	V
		BC547, BC550	50	-	
		BC548, BC549	30	-	
Collector Emitter Breakdown Voltage at $I_C = 1\text{ mA}$	$V_{(BR)CEO}$	BC546	65	-	V
		BC547, BC550	45	-	
		BC548, BC549	30	-	
Emitter Base Breakdown Voltage at $I_E = 10\text{ }\mu\text{A}$	$V_{(BR)EBO}$	6	-	V	

## BC546...BC550

### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Collector Emitter Saturation Voltage at $I_C = 10\text{ mA}$ , $I_B = 0.5\text{ mA}$ at $I_C = 100\text{ mA}$ , $I_B = 5\text{ mA}$	$V_{CE(sat)}$	-	0.25 0.6	V
Base Emitter On Voltage at $V_{CE} = 5\text{ V}$ , $I_C = 2\text{ mA}$ at $V_{CE} = 5\text{ V}$ , $I_C = 10\text{ mA}$	$V_{BE(on)}$	0.55	0.7 0.77	V
Transition Frequency at $V_{CE} = 5\text{ V}$ , $I_C = 10\text{ mA}$ , $f = 100\text{ MHz}$	$f_T$	100	-	MHz
Collector Base Capacitance at $V_{CB} = 10\text{ V}$ , $f = 1\text{ MHz}$	$C_{cb}$	-	6	pF

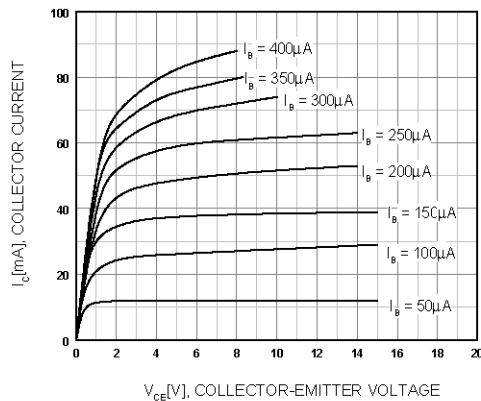


Figure 1. Static Characteristic

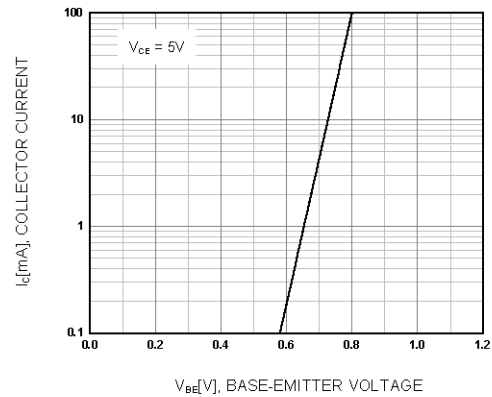


Figure 2. Transfer Characteristic

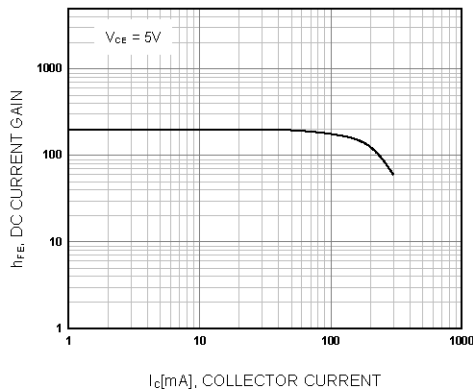


Figure 3. DC current Gain

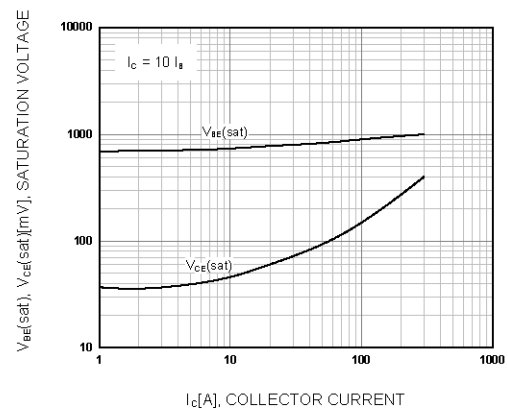


Figure 4. Base-Emitter Saturation Voltage  
Collector-Emitter Saturation Voltage